

**JIEJIE MICROELECTRONICS CO., LTD**

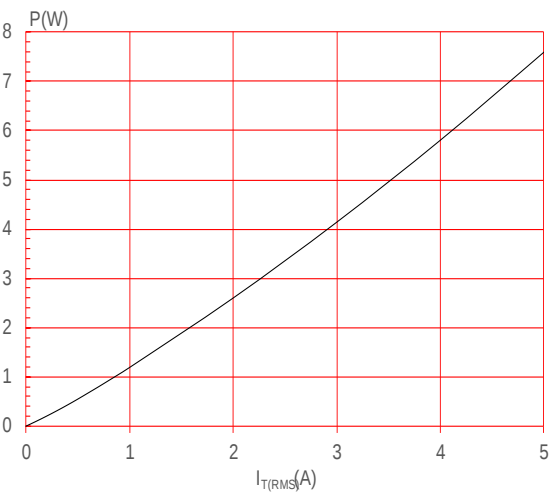
|                                                                                            |             |     |    |
|--------------------------------------------------------------------------------------------|-------------|-----|----|
| Average gate power dissipation ( $T_j=125\text{ }^{\circ}\text{C}$ )                       | $P_{G(AV)}$ | 0.5 | W  |
| Peak gate power                                                                            | $P_{GM}$    | 10  | W  |
| Peak pulse voltage<br>( $T_j=25\text{ }^{\circ}\text{C}$ ; non-repetitive,off-state;FIG.7) | $V_{pp}$    | 3.5 | kV |

( $T_j=25\text{ }^{\circ}\text{C}$  unless otherwise specified)

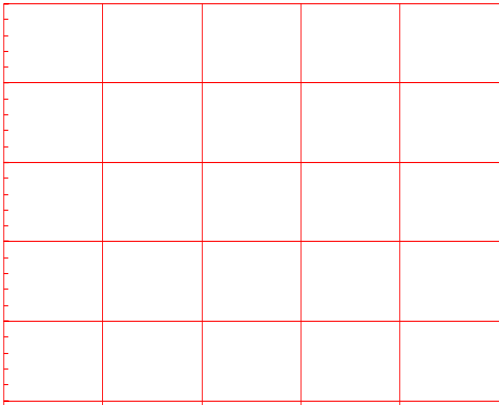
| Symbol   | Test Condition                                                     | Quadrant | Value |     | Unit |
|----------|--------------------------------------------------------------------|----------|-------|-----|------|
| $I_{GT}$ | $V_D=12V\ R_L=33\Omega$                                            | - -      | MAX.  | 25  | mA   |
| $V_{GT}$ |                                                                    | - -      | MAX.  | 1   | V    |
| $V_{GD}$ | $V_D=V_{DRM}\ T_j=125\text{ }^{\circ}\text{C}$<br>$R_L=3.3k\Omega$ | - -      | MIN.  | 0.2 | V    |
| $I_L$    | $I_G=1.2I_{GT}$                                                    | -        | MAX.  | 40  | mA   |



**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature



**ACJT425-10A**





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